1SS355 Silicon Epitaxial Planar Switching Diode

Features

- Small plastic package suitable for surface mounted design
- High reliability with high surge current handling capability

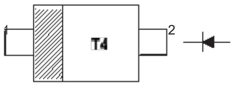
Applications

- High speed switching

MARKING:T4

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Top View

Marking Code: "T4"

Simplified outline SOD- 23 and symbol

Absolute Maximum Ratings $(T_a = 25_{o}C)$

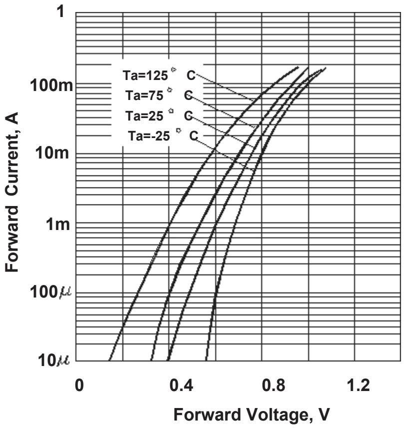
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	90	V
Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	100	mA
Peak Forward Current	I_{FM}	225	mA
Surge Forward Current (1 s)	I_{FSM}	500	mA
Junction Temperature	T_j	150	$_o$C
Storage Temperature Range	T_{stg}	- 55 to + 150	$_o$C

Electrical Characteristics $(T_a = 25_{o}C)$

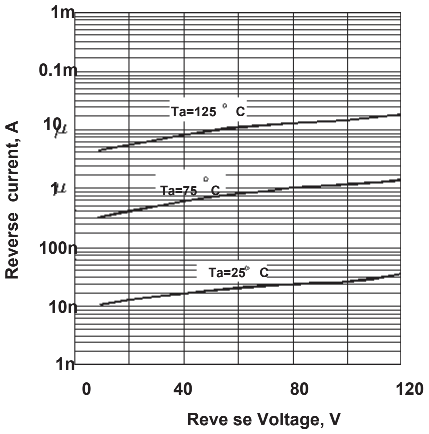
Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	1.2	V
Reverse Current at V_R = 80 V	I_R	0.1	μA
Capacitance between Terminals at V_R = 0.5 V, f = 1 MHz	C_T	3	pF
Reverse Recovery Time at V_R = 6 V, I_F = 10 mA, R_L = 100	t_{rr}	4	ns

Typical Characteristics

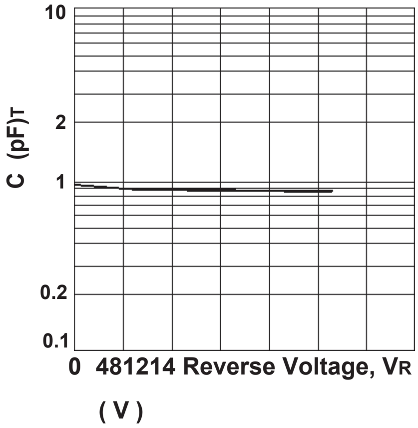
Forward Characteristics



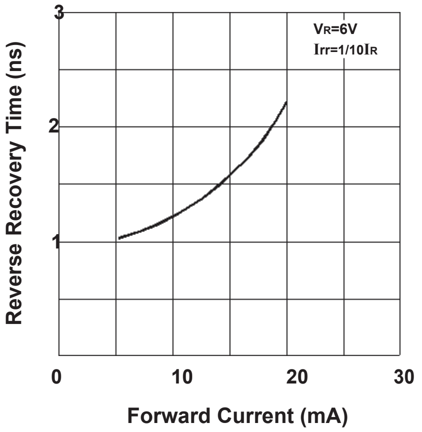
Reverse Characteristics



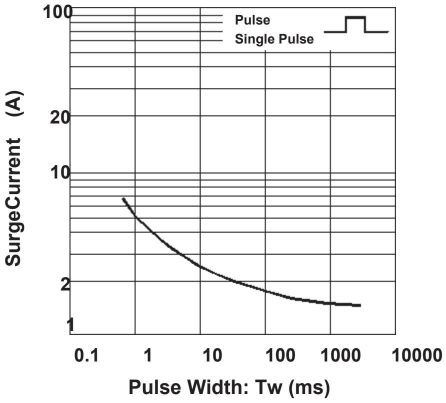
Capacitance between terminals characteristics



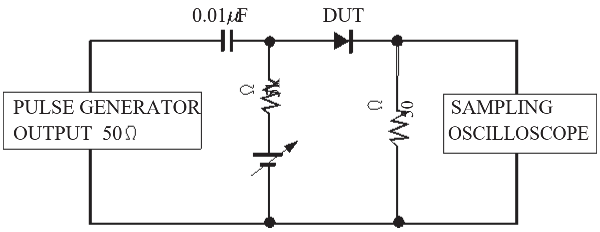
Reverse Recovery Time Characteristics



Surge Current Characteristics



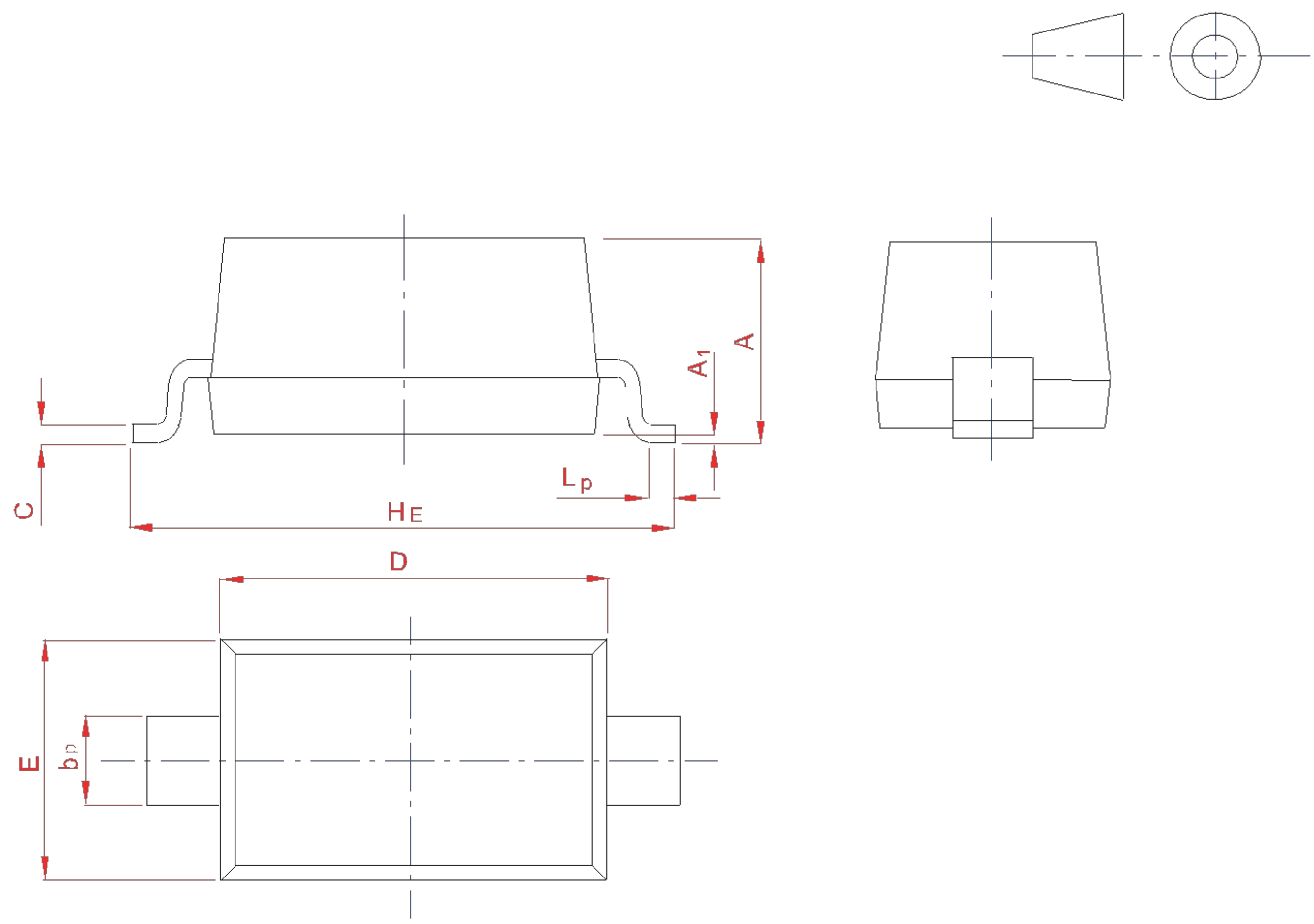
Reverse Recovery Time Measurement Circuit



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	b_p	C	D	E	H_E	A_1	L_p
mm	1.20 0.90	0.60 0.50	0.135 0.100	2.75 2.55	1.65 1.55	3.85 3.55	0.10 0.01	0.50 0.20